

RESPONSE TO RESTRICTION REQUIREMENT AND PRELIMINARY AMENDMENT

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Title: CONTACT STRUCTURE

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or more layers including platinum-iridium; and
an structure encircling the one or more layers.

Sub D18
98. (New) The integrated circuit of claim 97, wherein one of the one or more layers comprises a layer of tungsten nitride having a thickness of between about 900 angstroms and 1100 angstroms.

99. (New) The integrated circuit device of claim 97, wherein the second device is a bipolar transistor.

Sub D18
100. (New) An integrated circuit comprising:
a first device;
a second device;
one or more layers coupling the first device to the second device, at least one of the one or more layers including platinum-rhodium; and
a structure encircling at least two of the one or more layers.

Sub D20
101. (New) The integrated circuit of claim 100, wherein the one or more layers includes a polysilicon layer.

102. (New) The integrated circuit of claim 100, wherein the first device is formed in a substrate, the substrate selected from a group consisting of silicon, germanium, gallium-arsenide, and silicon-on-sapphire.

Claims 94-102 have been added; as a result, claims 19-36 and 94-102 are now pending in this application. The added claims are supported in the specification as originally filed. No new matter has been added.